

BLF8G20LS-160V

Power LDMOS transistor

Rev. 2 — 24 June 2014

Product data sheet

1. Product profile

1.1 General description

160 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25\text{ °C}$ in a common source class-AB production test circuit.

Test signal	f (MHz)	I _{DQ} (mA)	V _{DS} (V)	P _{L(AV)} (W)	G _p (dB)	η _D (%)	ACPR (dBc)
2-carrier W-CDMA	1805 to 1880	800	28	35.5	20	34	-29 [1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing = 5 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

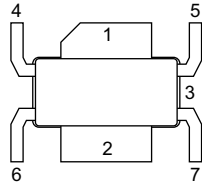
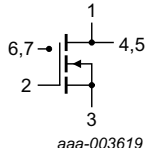
1.3 Applications

- RF power amplifier for multi systems base stations and multi carrier applications in the 1800 MHz to 2000 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		 aaa-003619
2	gate		
3	source [1]		
4	decoupling lead		
5	decoupling lead		
6	n.c.		
7	n.c.		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF8G20LS-160V	-	earless flanged LDMOST ceramic package; 6 leads	SOT1239B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature [1]		-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$; $P_L = 25\text{ W}$; $V_{DS} = 28\text{ V}$; $I_{Dq} = 800\text{ mA}$	0.290	K/W

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ °C}$, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 1.8\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 180\text{ mA}$	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28\text{ V}; I_D = 800\text{ mA}$	1.7	2.1	2.5	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	3.6	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; V_{DS} = 10\text{ V}$	-	33.8	-	A
I_{GSS}	gate leakage current	$V_{GS} = 9\text{ V}; V_{DS} = 0\text{ V}$	-	-	360	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 180\text{ mA}$	-	1.6	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; I_D = 6.3\text{ A}$	-	0.07	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; PAR = 8.4 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 DPCH; $f_1 = 1807.5\text{ MHz}; f_2 = 1812.5\text{ MHz}; f_3 = 1872.5\text{ MHz}; f_4 = 1877.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}; I_{Dq} = 800\text{ mA}; T_{case} = 25\text{ °C}$; unless otherwise specified; in a production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 35.5\text{ W}$	19	20	-	dB
η_D	drain efficiency	$P_{L(AV)} = 35.5\text{ W}$	30	34	-	%
RL_{in}	input return loss	$P_{L(AV)} = 35.5\text{ W}$	-	-10	-7	dB
ACPR	adjacent channel power ratio	$P_{L(AV)} = 35.5\text{ W}$	-	-29	-25	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF8G20LS-160V is capable of withstanding a load mismatch corresponding to $V_{SWR} = 10 : 1$ through all phases under the following conditions: $V_{DS} = 28\text{ V}; I_{Dq} = 800\text{ mA}; P_L = 140\text{ W (CW)}; f = 1805\text{ MHz}$.

7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data; $I_{Dq} = 800\text{ mA}; V_{DS} = 28\text{ V}$; typical values unless otherwise specified.

f (MHz)	Z_S [1] (Ω)	Z_L [1] (Ω)
1805	1.248 – j3.066	1.19 – j2.749
1842.5	2.372 – j3.119	1.19 – j2.431
1880	3.025 – j4.124	1.19 – j2.431

[1] Z_S and Z_L defined in [Figure 1](#).

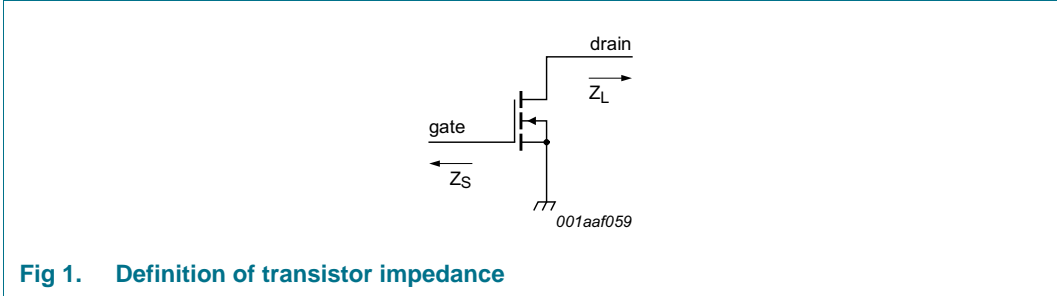


Fig 1. Definition of transistor impedance

7.3 VBW in a class-AB operation

The BLF8G20LS-160V has a video bandwidth of 70 MHz (typical) when measured in a class-AB test circuit operating at a center frequency of 1843 MHz for $V_{DS} = 28\text{ V}$ and $I_{Dq} = 800\text{ mA}$.

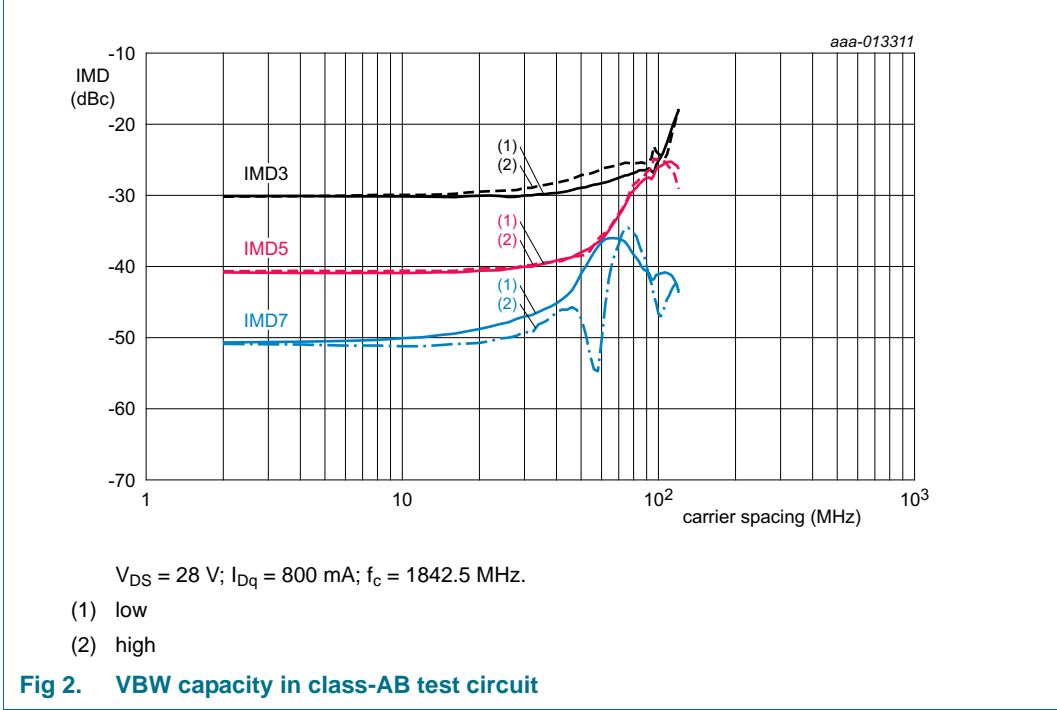


Fig 2. VBW capacity in class-AB test circuit

7.4 Test circuit

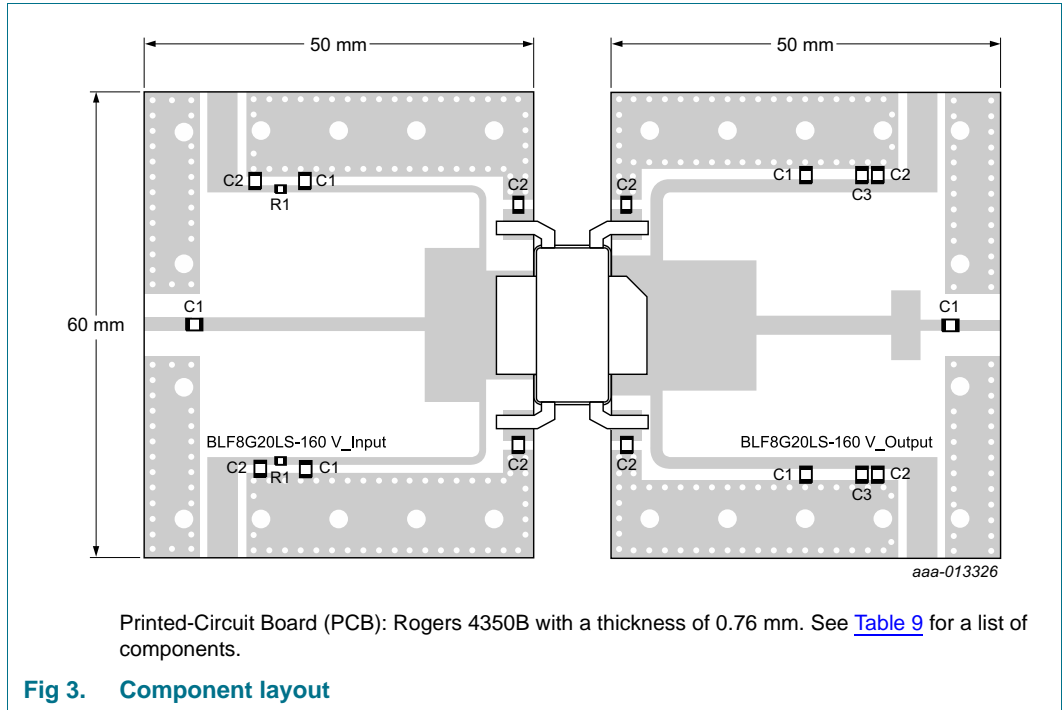


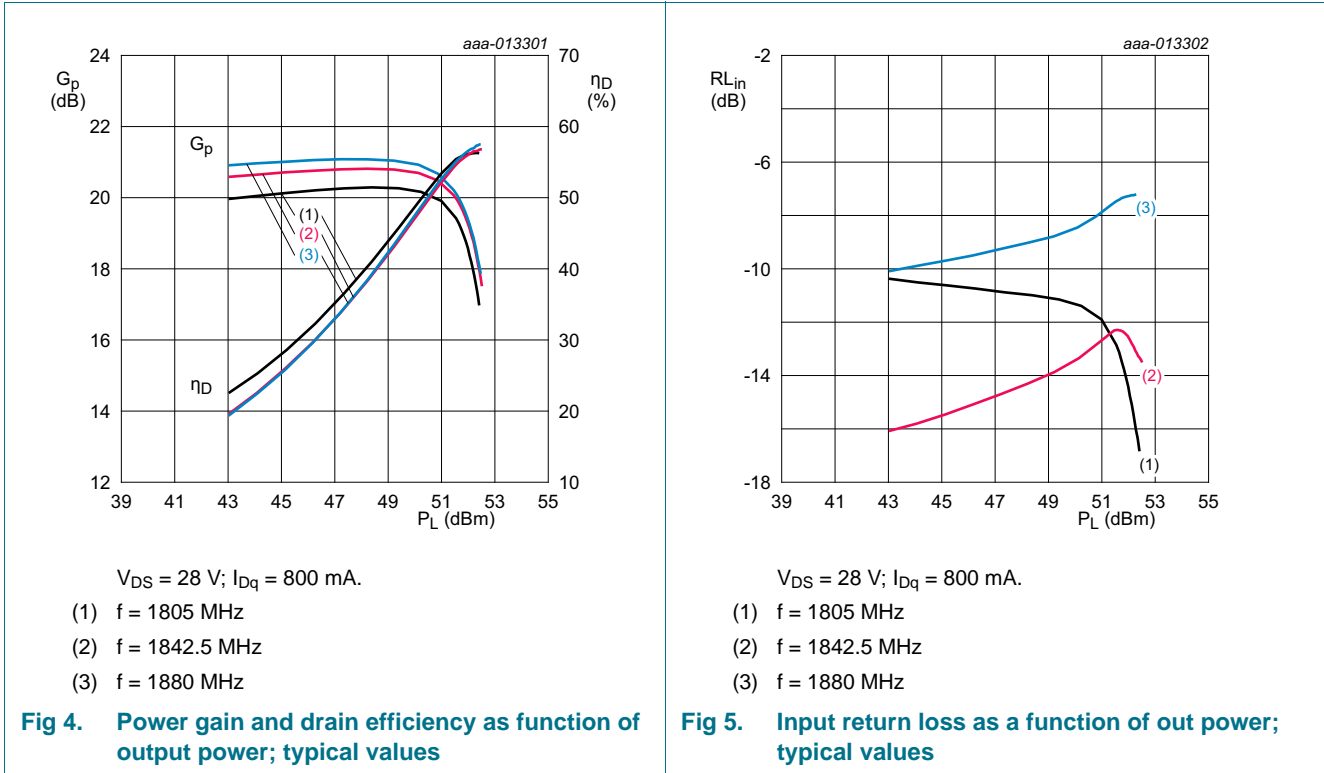
Table 9. List of components

See [Figure 3](#) for component layout.

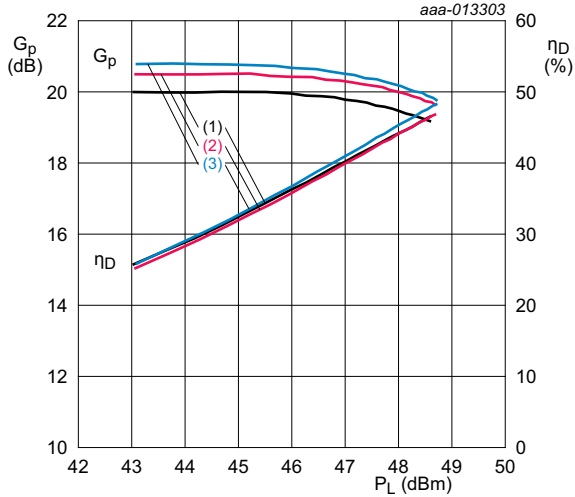
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	15 pF	ATC100B
C2	multilayer ceramic chip capacitor	10 μ F	Murata
C3	multilayer ceramic chip capacitor	2.2 μ F	Murata
R1	chip resistor	5.1 Ω	Vishay Dale SMD 0805

7.5 Graphical data

7.5.1 Pulsed CW

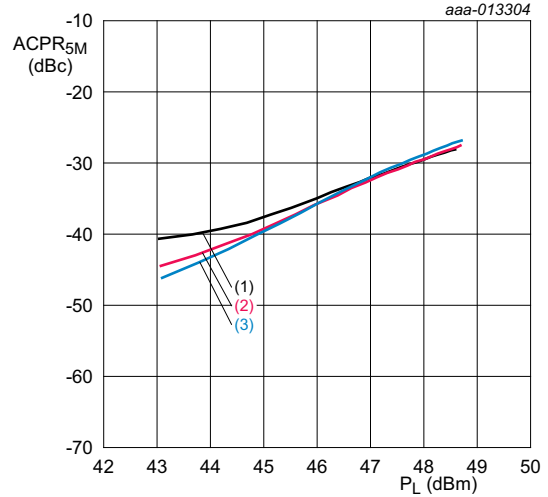


7.5.2 1-Carrier W-CDMA



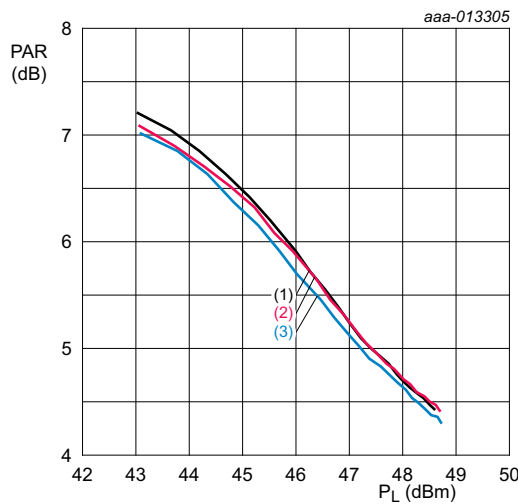
$V_{DS} = 28\text{ V}; I_{Dq} = 800\text{ mA}.$
 (1) $f = 1805\text{ MHz}$
 (2) $f = 1842.5\text{ MHz}$
 (3) $f = 1880\text{ MHz}$

Fig 6. Power gain and drain efficiency as a function of output power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 800\text{ mA}.$
 (1) $f = 1805\text{ MHz}$
 (2) $f = 1842.5\text{ MHz}$
 (3) $f = 1880\text{ MHz}$

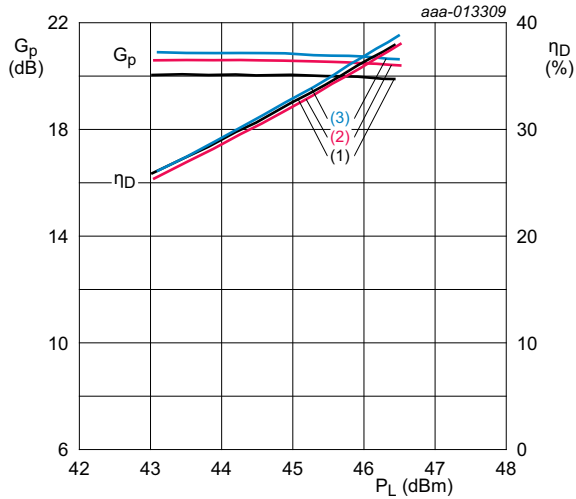
Fig 7. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 800\text{ mA}.$
 (1) $f = 1805\text{ MHz}$
 (2) $f = 1842.5\text{ MHz}$
 (3) $f = 1880\text{ MHz}$

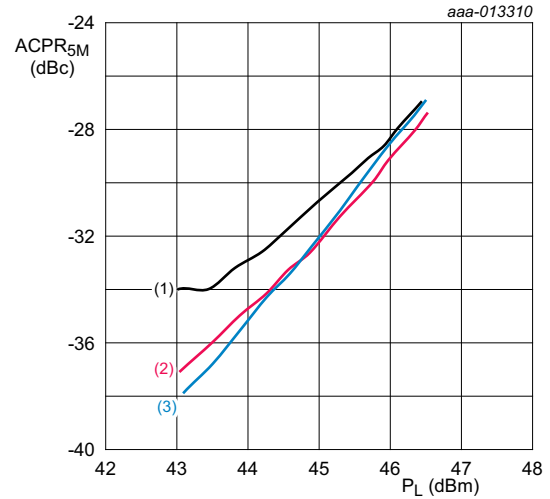
Fig 8. Peak-to-average ratio as a function of output power; typical values

7.5.3 2-Carrier W-CDMA



$V_{DS} = 28\text{ V}; I_{Dq} = 800\text{ mA}.$
 (1) $f = 1805\text{ MHz}$
 (2) $f = 1842.5\text{ MHz}$
 (3) $f = 1880\text{ MHz}$

Fig 9. Power gain and drain efficiency as function of output power; typical values



$V_{DS} = 28\text{ V}; I_{Dq} = 800\text{ mA}.$
 (1) $f = 1805\text{ MHz}$
 (2) $f = 1842.5\text{ MHz}$
 (3) $f = 1880\text{ MHz}$

Fig 10. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

8. Package outline

Earless flanged LDMOST ceramic package; 6 leads

SOT1239B

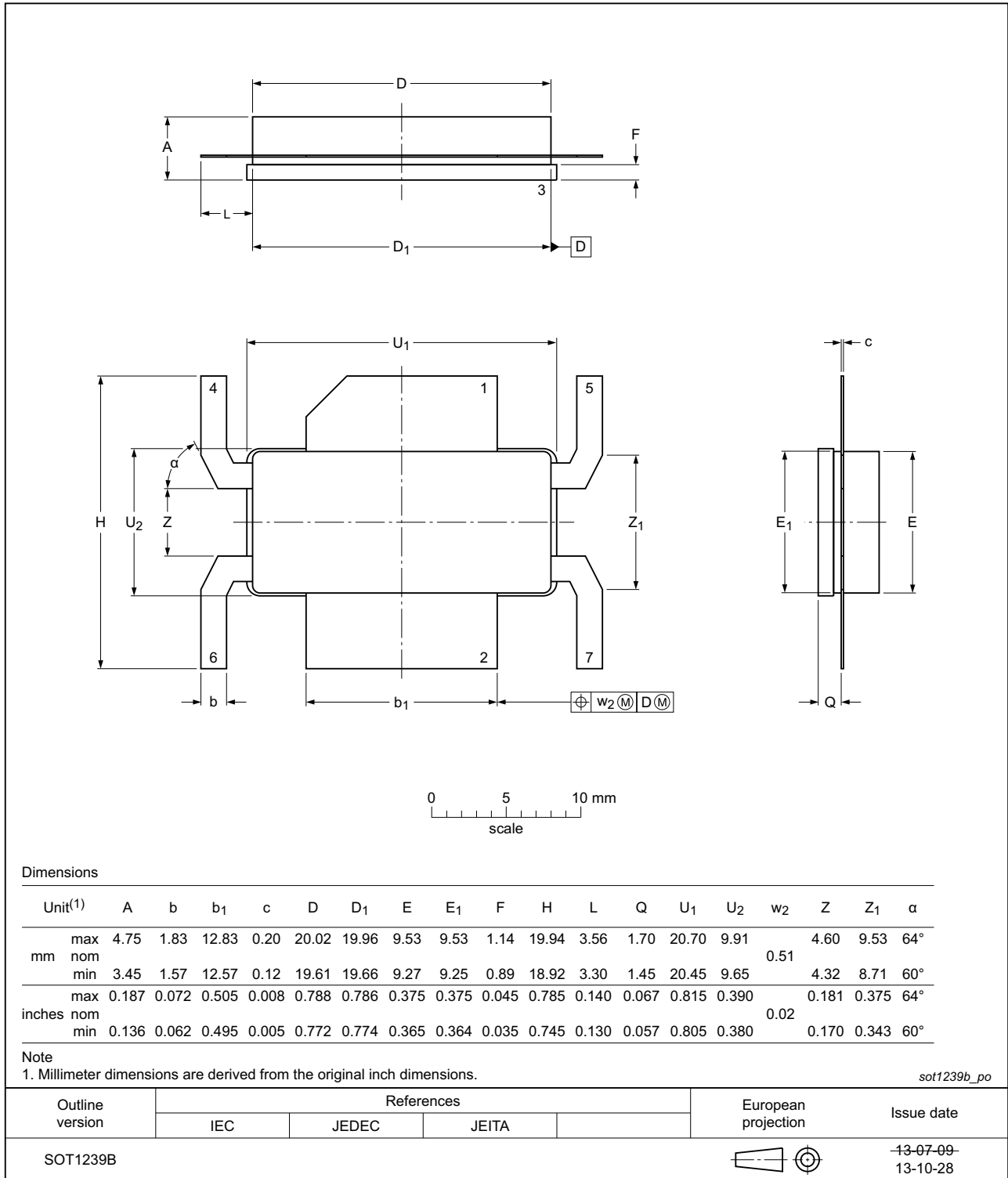


Fig 11. Package outline SOT1239B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G20LS-160V v.2	20140624	Product data sheet	-	BLF8G20LS-160V v.1
Modifications	<ul style="list-style-type: none"> • Section 1.3 on page 1: 'W-CDMA' changed to 'multi systems' • Table 5 on page 2: typical value added • Table 6 on page 3: table updated • Table 7 on page 3: table updated • Section 7 on page 3: section added 			
BLF8G20LS-160V v.1	20140305	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

1 Product profile 1

1.1 General description 1

1.2 Features and benefits 1

1.3 Applications 1

2 Pinning information 2

3 Ordering information 2

4 Limiting values 2

5 Thermal characteristics 2

6 Characteristics 3

7 Test information 3

7.1 Ruggedness in class-AB operation 3

7.2 Impedance information 3

7.3 VBW in a class-AB operation 4

7.4 Test circuit 5

7.5 Graphical data 6

7.5.1 Pulsed CW 6

7.5.2 1-Carrier W-CDMA 7

7.5.3 2-Carrier W-CDMA 8

8 Package outline 9

9 Handling information 10

10 Abbreviations 10

11 Revision history 10

12 Legal information 11

12.1 Data sheet status 11

12.2 Definitions 11

12.3 Disclaimers 11

12.4 Trademarks 12

13 Contact information 12

14 Contents 13

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